

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

**MANABE et al.**

Group Art Unit: 2811

**Divisional of**

Appln. No.: 09/417,778

Examiner: Tran, M.

Filed: Herewith

Title: LIGHT EMITTING SEMICONDUCTOR  
DEVICE USING GALLIUM NITRIDE GROUP COMPOUND

October 2, 2000

**PRELIMINARY AMENDMENT**

Honorable Commissioner of  
Patents and Trademarks,  
Washington, DC 20231

Sir:

Kindly enter the following preliminary amendments.

**IN THE TITLE:**

Please change the title to A METHOD FOR MANUFACTURING A GALLIUM NITRIDE GROUP COMPOUND SEMICONDUCTOR.

**IN THE CLAIMS:**

Please cancel claim 1 and add the attached new claims 19-118.

--19. A method for producing a gallium nitride group compound semiconductor by using an organometallic compound vapor phase epitaxy, comprising the steps of: